

Joonas Hilska

List of Publications by Year in descending order

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16
papers

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1307594

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citing authors

#	ARTICLE	IF	CITATIONS
1	High-Field Electron-Drift Velocity in n-Type Modulation-Doped GaAs _{0.96} Bi _{0.04} Quantum Well Structure. <i>Physica Status Solidi - Rapid Research Letters</i> , 2022, 16, .	2.4	2
2	Nanohole Etching in AlGaSb with Gallium Droplets. <i>Crystal Growth and Design</i> , 2021, 21, 1917-1923.	3.0	11
3	Highly uniform GaSb quantum dots with indirect-to-direct bandgap crossover at telecom range. <i>APL Materials</i> , 2021, 9, .	5.1	12
4	A quantitative analysis of electronic transport in n- and p-type modulation-doped GaAsBi/AlGaAs quantum well structures. <i>Semiconductor Science and Technology</i> , 2021, 36, 115017.	2.0	4
5	Electronic transport in n-type modulation-doped AlGaAs/GaAsBi quantum well structures: influence of Bi and thermal annealing on electron effective mass and electron mobility. <i>Semiconductor Science and Technology</i> , 2020, 35, 025009.	2.0	10
6	Raman spectroscopy of GaSb _{1-x} Bi _x alloys with high Bi content. <i>Applied Physics Letters</i> , 2020, 116, .	3.3	6
7	The role of As species in self-catalyzed growth of GaAs and GaAsSb nanowires. <i>Nanotechnology</i> , 2020, 31, 465601.	2.6	4
8	Power loss mechanisms in n-type modulation-doped AlGaAs/GaAsBi quantum well heterostructures. <i>Semiconductor Science and Technology</i> , 2020, 35, 095038.	2.0	5
9	Impact of Bi incorporation on the evolution of microstructure during growth of low-temperature GaAs:Bi/Ga(As,Bi) layers. <i>Journal of Applied Physics</i> , 2019, 126, 085305.	2.5	7
10	Analysis of GaAsBi growth regimes in high resolution with respect to As/Ga ratio using stationary MBE growth. <i>Journal of Crystal Growth</i> , 2019, 511, 33-41.	1.5	13
11	Epitaxial phases of high Bi content GaSbBi alloys. <i>Journal of Crystal Growth</i> , 2019, 516, 67-71.	1.5	5
12	Optimization of Ohmic Contacts to p-GaAs Nanowires. <i>Nanoscale Research Letters</i> , 2019, 14, 344.	5.7	3
13	Optical properties of n- and p-type modulation doped GaAsBi/AlGaAs quantum well structures. <i>Journal of Alloys and Compounds</i> , 2018, 739, 987-996.	5.5	16
14	Optical properties of GaAs _{1-x} Bi _x /GaAs quantum well structures grown by molecular beam epitaxy on (100) and (311)B GaAs substrates. <i>Semiconductor Science and Technology</i> , 2018, 33, 124015.	2.0	7
15	Exciton localization and structural disorder of GaAs _{1-x} Bi _x /GaAs quantum wells grown by molecular beam epitaxy on (311)B GaAs substrates. <i>Semiconductor Science and Technology</i> , 2018, 33, 084002.	2.0	5
16	The Role of Epitaxial Strain on the Spontaneous Formation of Bi-Rich Nanostructures in Ga(As,Bi) Epilayers and Quantum Wells. <i>Nanoscience and Nanotechnology Letters</i> , 2017, 9, 1132-1138.	0.4	5